



8th individual discussion

"GaN contact technology"

☿ Date and time: Friday, March 4, 2022,
13:00-16:30 ☿ Location: Online via Zoom

Development toward practical use of GaN power devices is actively underway. Good contact formation is essential to achieve low on-resistance and stable operation, but at present, the phenomena at the metal/GaN interface in GaN are not fully understood. Therefore, based on the overview of metal/GaN interface evaluation and p-GaN ohmic contact research, and with information provided by the participants, we will clarify the issues faced by experts involved in GaN contact technology and discuss future issues. Discuss the direction of research.

.....program.....

13:00☿13:10 Opening remarks, explanation of today's

progress 13:10☿13:40 Development of p-GaN ohmic contact (tentative title)

Yasuo Koide (NIMS)

13:40☿14:10 GaN Schottky junction evaluation (tentative title)

Kenji Shiohima (Fukui University)

14:10☿14:40 Contact formation by tunnel junction to GaN (tentative title)

Tetsuya Takeuchi (Meijo University)

14:40-14:50 Break

14:50-16:20 Information provision and discussion from

participants 16:20-16:30 Closing remarks

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☿About participation: This is a discussion group where everyone can participate to discuss GaN contact formation technology. Participation solely for information gathering is not permitted. WEB

When you apply to participate, please fill out a form to input questions in advance about what you can discuss, the outline of your research, and the topics you can provide.

Please fill in the form. If there are a large number of applications, participants will be selected based on the questionnaire submitted at the time of application. Also, depending on the participants

To encourage lively discussion, please prepare 1-3 slides for presentation on the day. Please note.

☿Participation registration: Please register your participation using the web participation registration system (click here). Deadline: February 14, 2022 (Monday). If this guide is printed,

Please access from <https://formok.com/f/mtqpm67s>.

☿Participation fee: (tax included) After applying for participation, we will inform you about online payment.

Advanced Power Semiconductor Subcommittee members: 2,000 yen, General: 4,000 yen, Students: 1,000 yen

*Handouts will be distributed on Friday, February 25, 2022. No refunds will be accepted after this time.

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